

# LL4150

## FEATURES :

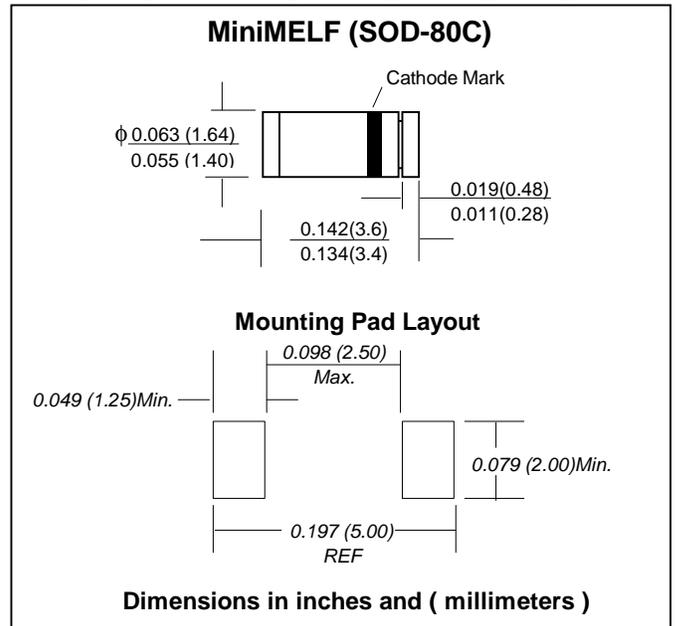
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 50 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 600 mA
- Pb / RoHS Free

## MECHANICAL DATA :

**Case:** MiniMELF Glass Case (SOD-80)

**Weight:** approx. 0.05g

## HIGH SPEED SWITCHING DIODE



## Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

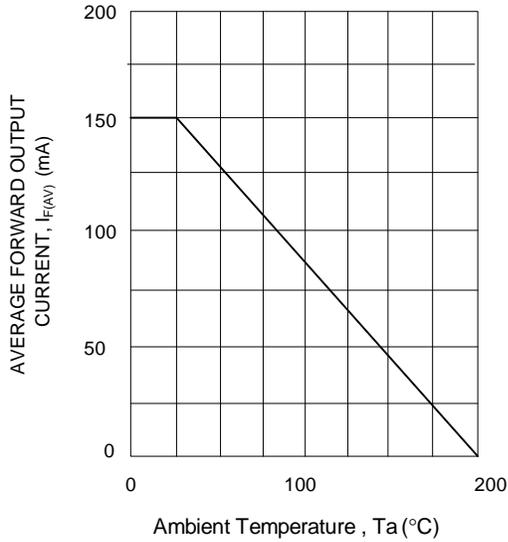
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	75	V
Maximum Reverse Voltage	$V_R$	50	V
Maximum Continuous Current	$I_F$	200	mA
Maximum Average Forward Current	$I_{F(AV)}$	150	mA
Maximum Surge Forward Current at $t < 1s$ and $T_j = 25^\circ C$	$I_{FSM}$	0.5	A
Maximum Power Dissipation	$P_D$	500	mW
Maximum Repetitive Peak Forward Current	$I_{FRM}$	600	mA
Thermal Resistance Junction to Ambient Air <sup>(1)</sup>	$R_{\theta JA}$	350	$^\circ C/W$
Maximum Junction Temperature	$T_J$	175	$^\circ C$
Storage Temperature Range	$T_S$	-65 to + 175	$^\circ C$

## Electrical Characteristics ( $T_J = 25^\circ C$ unless otherwise noted)

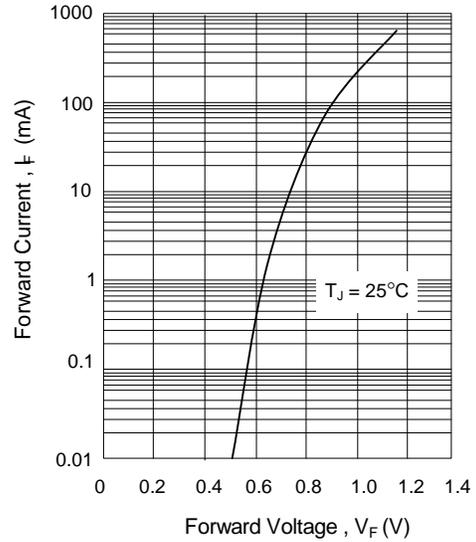
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Current	$I_R$	$V_R = 50 V$	-	-	0.1	$\mu A$
		$V_R = 50 V, T_j = 150^\circ C$	-	-	100	$\mu A$
Forward Voltage	$V_F$	$I_F = 100 mA$	-	-	0.92	V
		$I_F = 200 mA$	-	-	1.0	V
Diode Capacitance	$C_d$	$f = 1MHz; V_R = 0$	-	-	2.5	pF
Reverse Recovery Time	$T_{rr}$	$I_F = 10 mA$ to 200 mA to $I_R = 10 mA$ to 200 mA; $R_L = 100 \Omega$ ; measured at $I_R = 0.1 \times I_F$	-	-	4	ns

### RATING AND CHARACTERISTIC CURVES ( LL4150 )

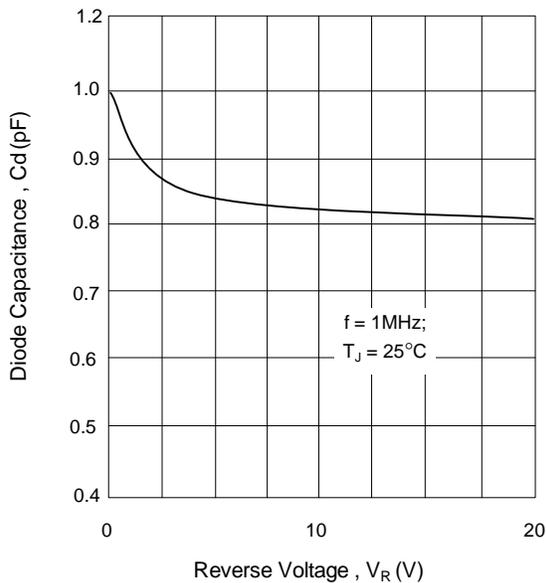
**FIG. 1 MAXIMUM FORWARD CURRENT VERSUS AMBIENT TEMPERATURE**



**FIG. 2 TYPICAL FORWARD VOLTAGE**



**FIG. 3 TYPICAL DIODE CAPACITANCE AS A FUNCTION OF REVERSE VOLTAGE**



**FIG. 4 TYPICAL REVERSE CURRENT VERSUS JUNCTION TEMPERATURE**

